2SC2619

Silicon NPN Epitaxial

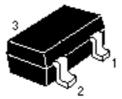
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Application

High frequency amplifier

Outline

MPAK



- 1. Emitter
- 2.Base
- 3. Collector



2SC2619

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V _{CEO}	30	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I _c	100	mA
Collector power dissipation	P _c	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Electrical Characteristics ($Ta = 25^{\circ}C$)

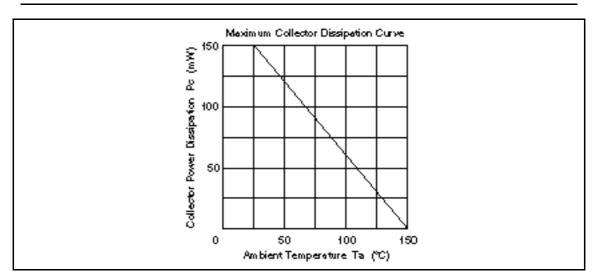
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	_	_	V	$I_{c} = 10 \ \mu\text{A}, \ I_{e} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	30	_	_	V	$I_C = 1 \text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	V	$I_{E} = 10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	0.5	μA	$V_{CB} = 20 \text{ V}, I_{C} = 0$
Emitter cutoff current	I _{EBO}	_	_	0.5	μA	$V_{EB} = 2 \text{ V}, I_{C} = 0$
DC current transfer ratio	h _{FE} *1	35	_	200		V_{CE} = 12 V, I_{C} = 2 mA
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	1.1	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
Base to emitter voltage	V_{BE}	_	_	0.75	V	$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$
Gain bandwidth product	f _T	_	230	_	MHz	$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$
Collector output capacitance	Cob	_	_	3.5	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$
Noise figure	NF	_	5.0	_	dB	$V_{CE} = 6 \text{ V}, I_{C} = 2 \text{ mA},$ $f = 1 \text{ MHz}, R_{g} = 500$

Note: 1. The 2SC2619 is grouped by h_{FE} as follows.

Grade	Α	В	С
Mark	FA	FB	FC
h _{FE}	35 to 75	60 to 120	100 to 200

See characteristic curves of 2SC460.

2SC2619



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